

Silicon NPN Transistors



BCE

- . With TO-220Fa package
- . Low frequency power amplifiers and low-speed switching
- . Complement to type 2SB1097

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	100	V
V_{CEO}	Collector to emitter voltage	60	V
V_{EBO}	Emitter to base voltage	7	V
I_C	Collector current	7	A
I_{CP}	Collector current-Pluse	15	A
P_C	Collector power dissipation	30	W
T_j	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~150	°C

TO-220Fa

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_{CBO}	Collector cut-off current	$V_{CB}=80V, I_E=0;$			10	μA
I_{EBO}	Emitter ut-off current	$V_{EB}=5V, I_C=0$			10	μA
V_{CBO}	Collector-base breakdown voltage					
V_{CEO}	Collector-emitter sustaining voltage	$I_C=30mA; I_B=0$	60			V
V_{EBO}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	$I_C=5A; I_B=0.5A$			0.5	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	$I_C=3A; V_{CE}=1V$	40		200	
h_{FE-2}	Forward current transfer ratio	$I_C=5A; V_{CE}=1V$	20			
$V_{BE(sat-1)}$	Base-emitter saturation voltages	$I_C=5A; I_B=0.5A$			1.5	V
$V_{BE(sat-2)}$	Base-emitter saturation voltages					

M	L	K
40-80	60-120	100-200